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IN THE SPECIFICATION:

Please amend the specification as follows:

Please replace the paragraph beginning on page 18, line 21, and ending on page 19, line 14, which begins with the phrase "According to one method of the invention," with the following paragraph:

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-- According to one method of the invention, base substrate **12** and a Group III metal target are loaded into a sputter deposition chamber. A highly energetic plasma-enhanced environment is generated in the chamber, using a suitable background gas such as argon. Separate nitrogen-containing source gas is conducted into the chamber. Alternatively, the gas utilized to generate the plasma could also be used as the reactant source gas, in which case the background gas provides the nitrogen species. The Group III metal target is sputtered to produce a Group III metal source vapor. The Group III metal source vapor combines with the nitrogen-containing gas, which is characterized as including one or more species such as diatomic nitrogen, atomic nitrogen, nitrogen ions, and partially ionized nitrogen, as well as nitrogen-containing compounds such as ammonia. As a result, reactant vapor species comprising components of the Group III metal and the nitrogen are produced within the reaction chamber, and are deposited on growth surface **12A** of base substrate **12** (or on growth surface **16A** when first

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deposited buffer layer 16). The as-deposited reactant vapor species grows epitaxially on growth surface 12A to produce single-crystal M^{III}N layer 14. M^{III}N layer 14 can be doped by conducting conventional doping methods, such as by introducing dopant-containing gases into the reaction chamber under controlled conditions. Accordingly, M^{III}N layer 14 can comprise an intrinsic M^{III}N material, a doped M^{III}N material, or an M^{III}N alloy or compound containing greater than 50% M^{III} and N. --